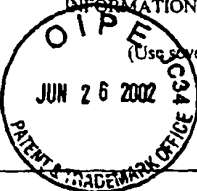


Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 110041		APPLICATION NO. 09/899,058	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary) 				APPLICANTS Satoshi INOUE et al.			
				FILING DATE July 6, 2001			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
JD		5,936,291	08/10/1999	Makita et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
JD		EP 0 166 208 A2	01/02/1986	Europe			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
EXAMINER				DATE CONSIDERED			
JD				10/21/03			
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Date: June 26, 2002

Sheet 1 of 1

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TD		✓ Ya-Chin KING et al., "MOS Memory Using Germanium Nanocrystals Formed by Thermal Oxidation of Si _{1-x} Ge _x ", IEDM, 1998 pp 115-118					
EXAMINER 2/2/03				DATE CONSIDERED 10/22/03			
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